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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

OHTAKE, Fumio et al.

Serial No.: **09/749,590**

Filed: **December 28, 2000**

For: **SEMICONDUCTOR DEVICE HAVING GATE ELECTRODES WITH POLYMETAL STRUCTURE OF POLYCRYSTALLINE SILICON FILMS AND METAL FILMS (as amended)**

Group Art Unit **2814**

Examiner: **MAI, Anh D.**
P.T.O. Confirmation No.: **4831**

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TECHNOLOGY CENTER 2800
OCT 14 2002
C. PAUL

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

October 2, 2002

Sir:

In response to the Office Action dated June 6, 2002, please amend the above-identified application as follows:

IN THE DRAWINGS:

Submitted herewith is a Request for Approval of Drawing Corrections, along with proposed drawing corrections to Figures 5, 6, 7, 8, 9 and 11, marked in red ink.

IN THE TITLE:

Amend the title of the invention, in its entirety, to read as follows:

~~SEMICONDUCTOR DEVICE HAVING GATE ELECTRODES WITH POLYMETAL~~
STRUCTURE OF POLYCRYSTALLINE SILICON FILMS AND METAL FILMS